

Synopsis V1.0
Single Event Transient and Destructive Testing of the
Texas Instrument SN74LVT244B Octal Buffer/Driver With 3-State Outputs

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Test Date: March 28, 2003

Report Date: April 14, 2003

I. Introduction

This study was undertaken to determine the single event destructive and transient susceptibility of the SN74LVT244B Octal Buffer/Driver. The device was monitored for transient interruptions in the output signal and for destructive events induced by exposing it to a heavy ion beam at the Texas A&M University Cyclotron Single Event Effects Test Facility.

II. Devices Tested

The sample size of the testing was two devices. The devices were manufactured by Texas Instruments and were characterized prior to exposure. The devices tested had a Lot Date Code of 0248TI.

III. Test Facility

Facility: Texas A&M University Cyclotron Single Event Effects Test Facility, 15 MeV/amu tune.

Flux: 4.38×10^4 to 5.05×10^5 particles/cm²/s.

Ion	LET (MeVcm ² /mg)
Ar	8.57
Kr	28.8
Xe	53.1

IV. Test Methods

The SN74LVT244B was tested with heavy ions. The basic block diagram showing the test configuration is shown in Figure 1 and the SN74LVT244B test circuit is shown in Figure 2. The Test Setup for the SN74LVT244B latch up and transient experiment consisted of a multi-channel power supply and a digitizing oscilloscope. Control of all test equipment was performed remotely via General Purpose Interface Bus (GPIB) with a Laptop computer as master. The devices on the test board (see Figure 2) consisted of a 74LS136 OR Gate, two SN74LVT244B (devices under test) and two 74LS85 comparators. All relevant equipment connections to the SN74LVT244B test board were made using scope probes.

A 74LS136 Exclusive OR Gate (see Figure 2) was used to provide inputs to the SN74LVT244B because it allows the test engineer to change the inputs simultaneously using one select line. This is necessary because the outputs of the SN74LVT244B can “hang up” due to the heavy ions, in that situation, the inputs to the SN74LVT244B can be change remotely by sending a positive edge pulse to produce a “soft reset” to the device. If the soft reset does not work, then power to the SN74LVT244B can be recycled to reset the device. The outputs of the SN74LVT244B never “hanged up” during testing so the soft reset circuit was never used.

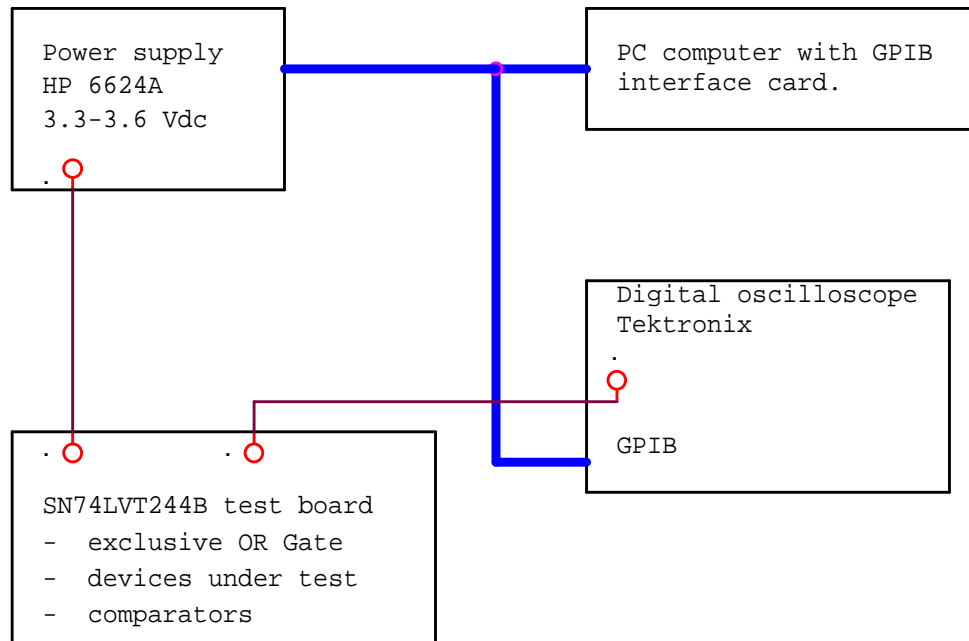


Figure 1. Block diagram for the test configuration for the SN74LVT244B.

Two 74LS85 comparators, which compares two four bit binary numbers, were used to monitor the outputs of the two SN74LVT244B. The P0, P1, P2, P3 inputs (see Figure 2) of the comparators were connected to the outputs of the two SN74LVT244B which is then compared to the Q0, Q1, Q2 and Q3 inputs of the comparators. The P=Q output of the comparators are a logic high when the P and the Q inputs are the same (e.g., no errors) and goes low when the inputs are different (e.g., error). The advantage derived from using a comparator is that all four outputs of the SN74LVT244B can be monitored at once with different input settings, which in our case is High, Low, High and Low.

The P=Q high outputs are monitored via channel 1 and channel two of the digital scope and the output voltage threshold was set at .25 to .3 volts below the monitored output. Throughout the experiment, only one P=Q output is monitored at a time. In the event of a transient, the P=Q high output would go low which will then trigger the set output voltage threshold. The output will then be captured and downloaded into the laptop computer via GPIB.

The voltage setting used for the output voltage threshold consisted of two different voltage levels. The reason for this is because the two comparators used have different P=Q high outputs. Comparator 1, which was used for DUT 1, has an output level of 4.7 volts with a set output voltage threshold of 4.5 volts. Comparator 2, which was used for DUT 2, has an output level of

4.5 volts with a set output voltage threshold of 4.2 volts. The delta was set to the lowest value where noise did not trigger events.

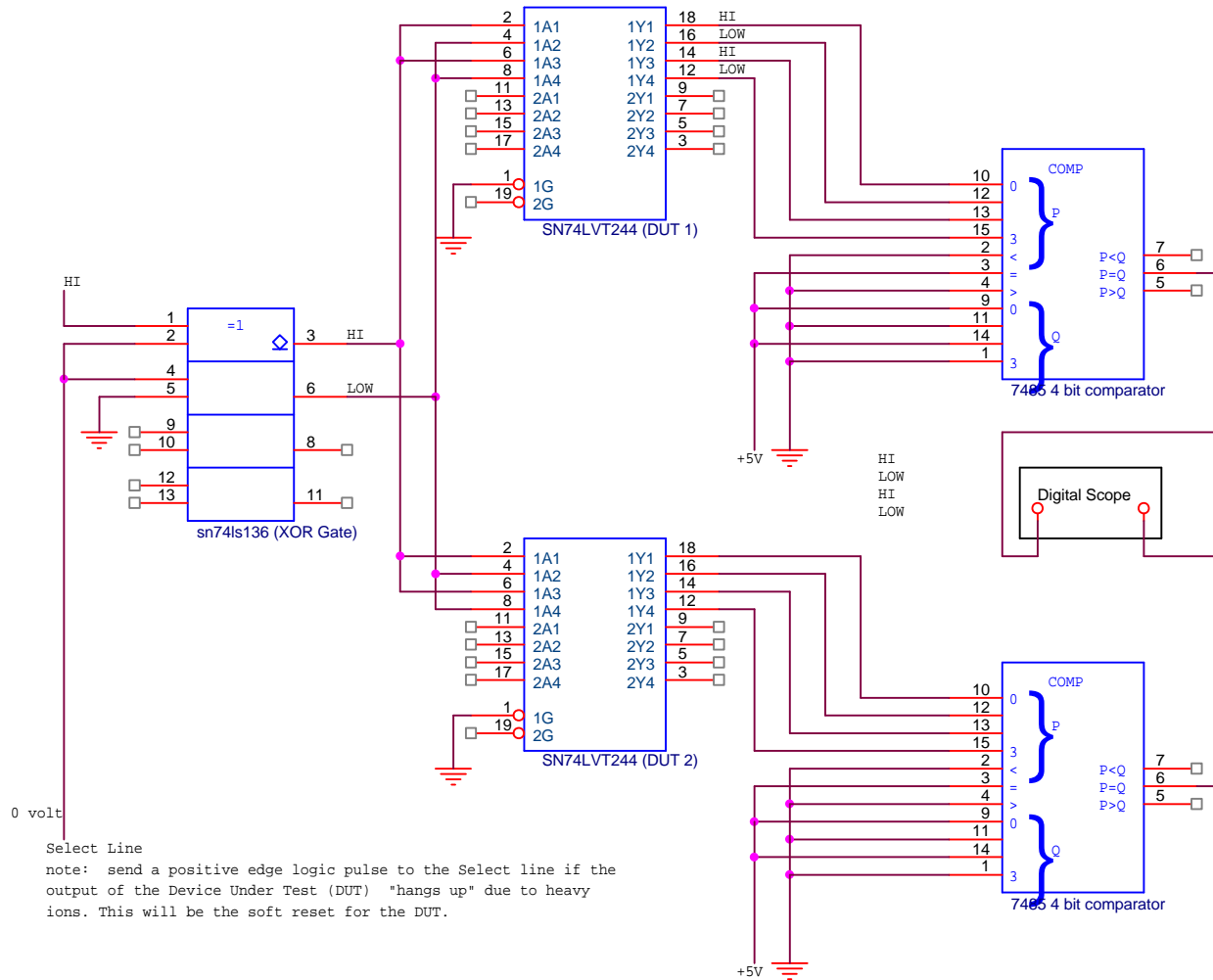


Figure 2. Schematic Diagram for the SN74LVT244B.

During the experiment, the SN74LVT244B was first tested with the voltage supply to the device set at 3.3 volts. After irradiation, the voltage supply was changed to 3.6 volts and the experiment was repeated. Latch up for the device under test was monitored by setting the power supply current limit to 80mA. If at any point the device starts to draw more than 80mA then the power supply will shut down automatically. The set power supply current limit was never exceeded during testing.

V. Results

During testing the two SN74LVT244B were irradiated with the Ar beam at both normal incidence and at 45 degrees (yielding an effective LET of approximately $8.57 \text{ MeV-cm}^2/\text{mg}$ and $12.12 \text{ MeV-cm}^2/\text{mg}$). Then the parts were also irradiated with the Kr and then Xe beams at normal incidence (yielding an effective LET of approximately $28.8 \text{ MeV-cm}^2/\text{mg}$ and $53.10 \text{ MeV-cm}^2/\text{mg}$). Testing was done for both parts with input voltages set to 3.3 volts and then 3.6 volts (for worst case latchup conditions). Transients from the SN74LVT244B were encountered with the Ar, Kr and Xe beams.

The two SN74LVT244B Octal Buffer/Driver Gates were tested to measure the latchup cross section under the above conditions. Each part was placed in the beam until a latch event occurred or 10^7 ions/cm² – the beam fluence was then recorded. During our experiment, no latchup event occurred.

The two SN74LVT244B Octal Buffer/Driver Gates were also tested to measure the transient cross section under the above conditions. Each part was placed in the beam until transient events occurred or 10^7 ions/cm² was reached. If many transients are present then a hundred samples are acquired and then the beam fluence was recorded. During our experiment, transient events occurred.

An average cross section was determined for a given LET as the number of transient events observed divided by the total fluence of all the runs at that LET. The cross section results are presented in Figure 3. A Weibull fit to the data gives an LET threshold for transient of approximately 5 MeV-cm²/mg and a saturation cross section is approximately 7.0×10^{-5} cm².

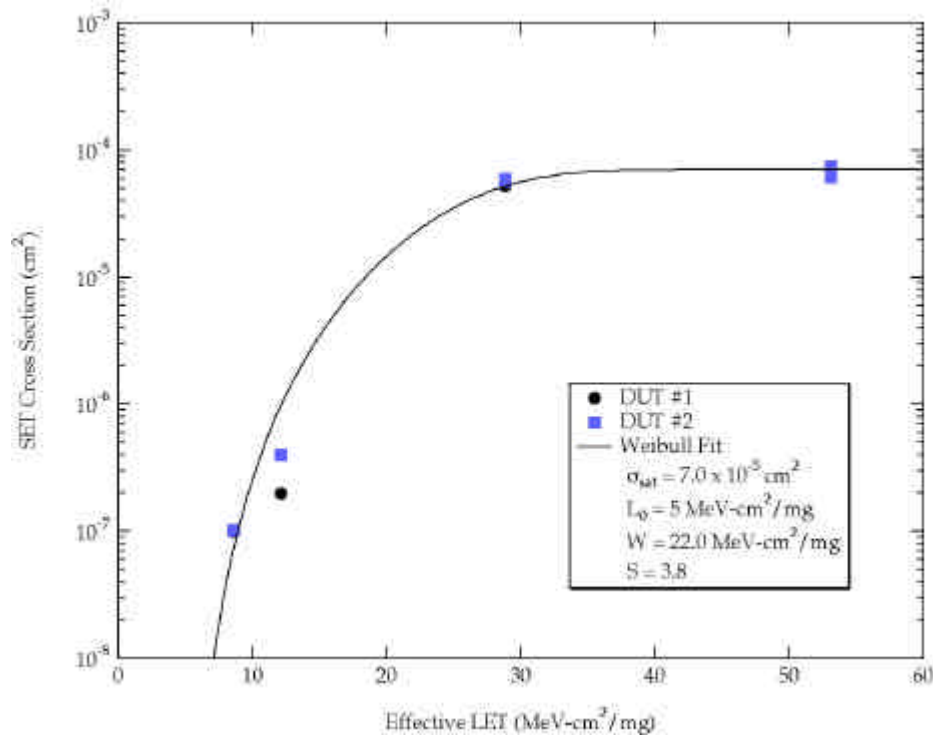


Figure 3. Transient cross section as a function of the effective LET for the SN74LVT244B Octal Buffer/Driver. The curve shows an approximate threshold of 5 MeV-cm²/mg and a saturation cross section of greater than 10^{-5} cm².

During the experiment, other logic bus buffers and logic gates were tested using the SN74LVT244B test board, and it was observed that the number of LETs seen in DUT socket 1 is consistently more than in DUT socket 2. The reason for this is concluded to be because the set output voltage threshold for DUT socket 1 is set at 200 mV below the output while the set output voltage threshold for DUT socket 2 is set at 300 mV below the output. This setting makes DUT socket 1 more sensitive to output transient by 100 mV than DUT socket 2. The reason the output

threshold for DUT 2 was set at 100 mV more than DUT 1 was because the output of the DUT 2 comparator was a little bit noisier.

Figure 4 shows a sample transient encountered during testing. The output captured is from the comparator not from the DUT itself. Lab testing of the comparators concluded that the heights of the transients from the comparators are directly related to the pulse width of the transients from the DUT itself. Using Figure 4 as an example we can conclude that the transient from the DUT was about 400 ns since the output of the comparator went below 0.8 volts. Figure 5 is also another example of a transient. The pulse width of this transient is about 300 ns.

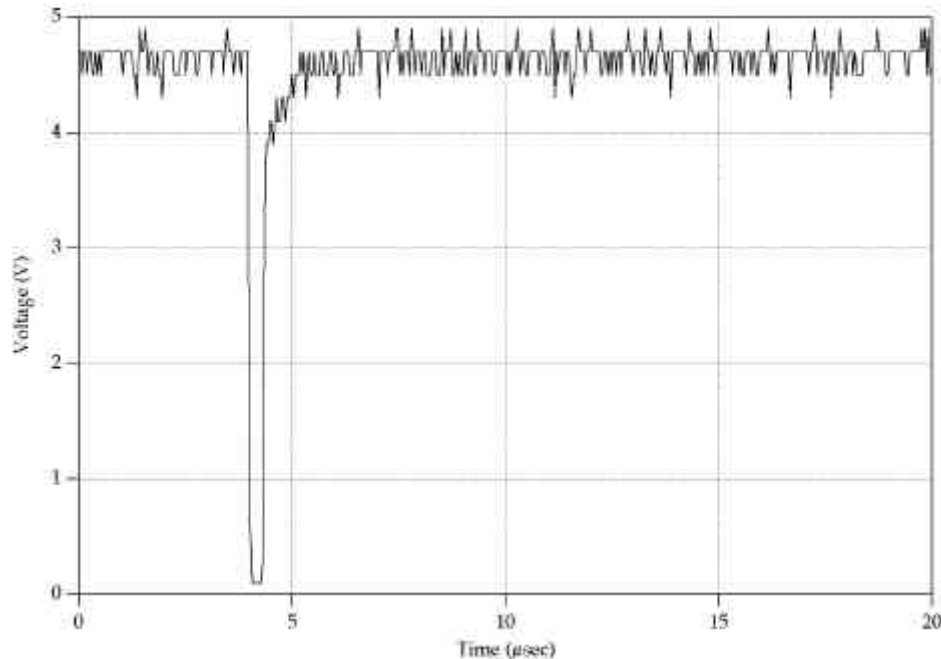


Figure 4. Transient taken from the output of the comparator, which was used to monitor the SN74LVT244B.

Since the heights of the transients stemming from the DUTs were not monitored during the experiment, we cannot determine the height of the transients by looking at the output of the comparators. But we can assume that voltage levels greater than 3.2 volts were considered high by the comparators and voltage levels below 0.7 volts were considered low (standard for TTL 74LS85 comparators).

Transients like the one in figure 4 and 5 were observed in the different beams use during the experiment. Even though there were transients present in the SN74LVT244B experiment and that some of the transients were about 400 ns in width, the results were still good because no device latchup occurred, the outputs did not hanged up and there were no destructive failure that resulted from the irradiation of the parts.

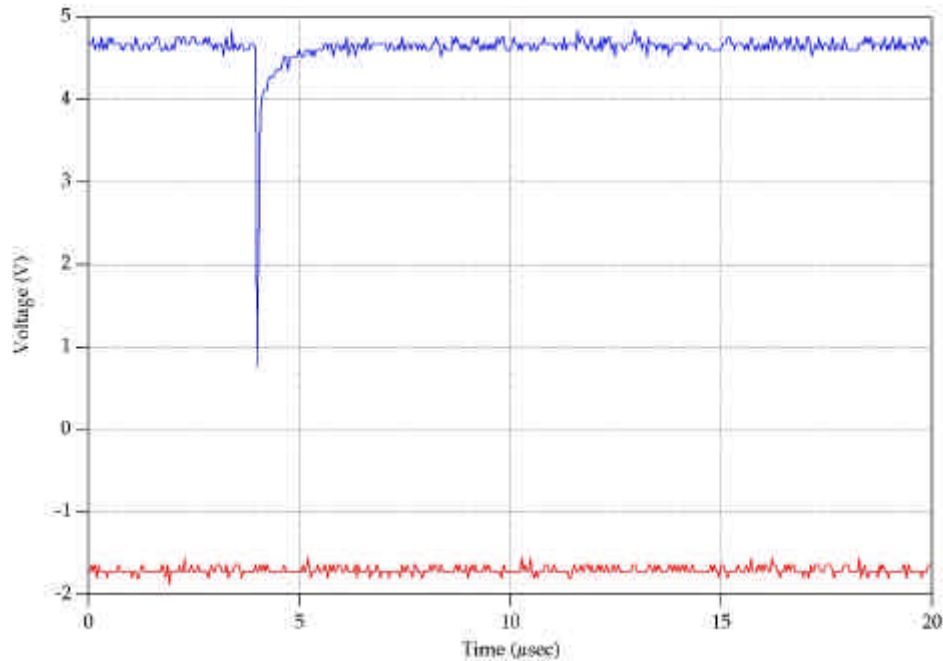


Figure 5. Another transient taken from the output of the comparator

VI. Recommendations

In general, devices are categorized based on heavy ion test data into one of the four following categories:

Category 1 – Recommended for usage in all NASA/GSFC spaceflight applications.

Category 2 – Recommended for usage in NASA/GSFC spaceflight applications, but may require mitigation techniques.

Category 3 – Recommended for usage in some NASA/GSFC spaceflight applications, but requires extensive mitigation techniques or hard failure recovery mode.

Category 4 – Not recommended for usage in any NASA/GSFC spaceflight applications.

The SN74LVT244B Octal Buffer/Drivers are Category 2 devices.